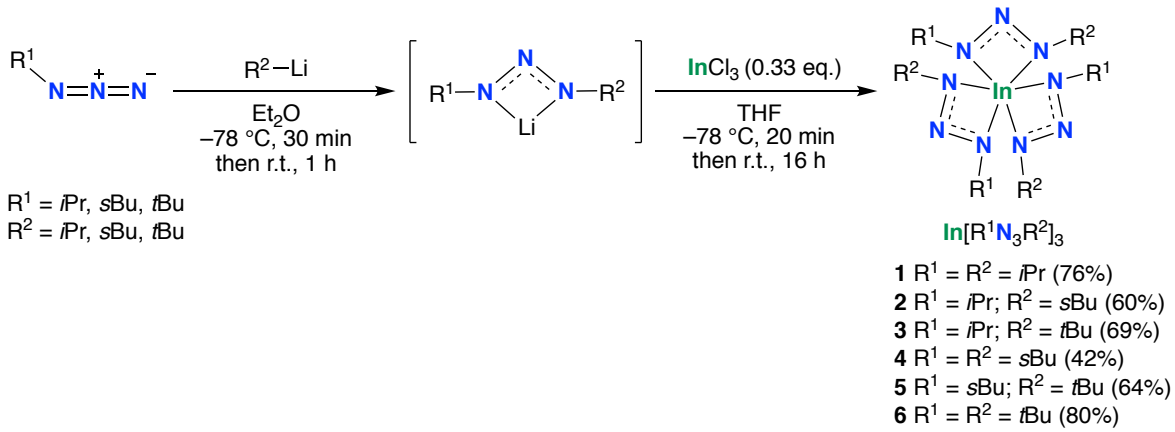

Scheme 1. Synthesis of indium(III) triazenide precursors **1-6**.

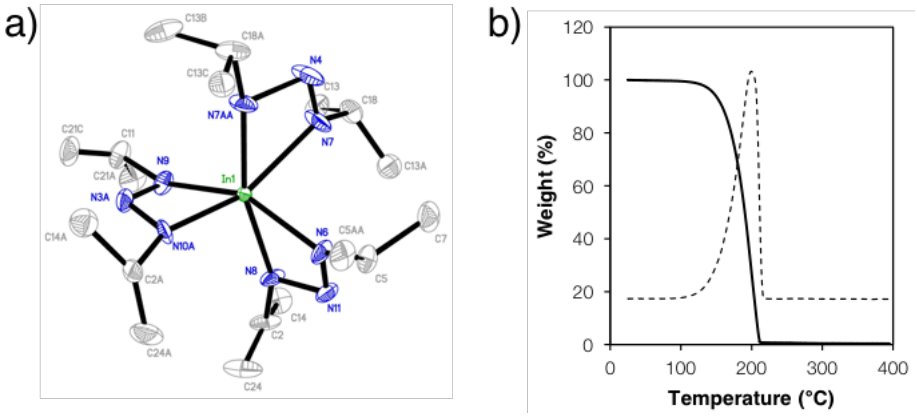

Figure 1. a) ORTEP drawing of **1** with thermal ellipsoids at the 50% probability level. All hydrogen atoms were removed for clarity. b) Thermogravimetric analysis of compound **1**.

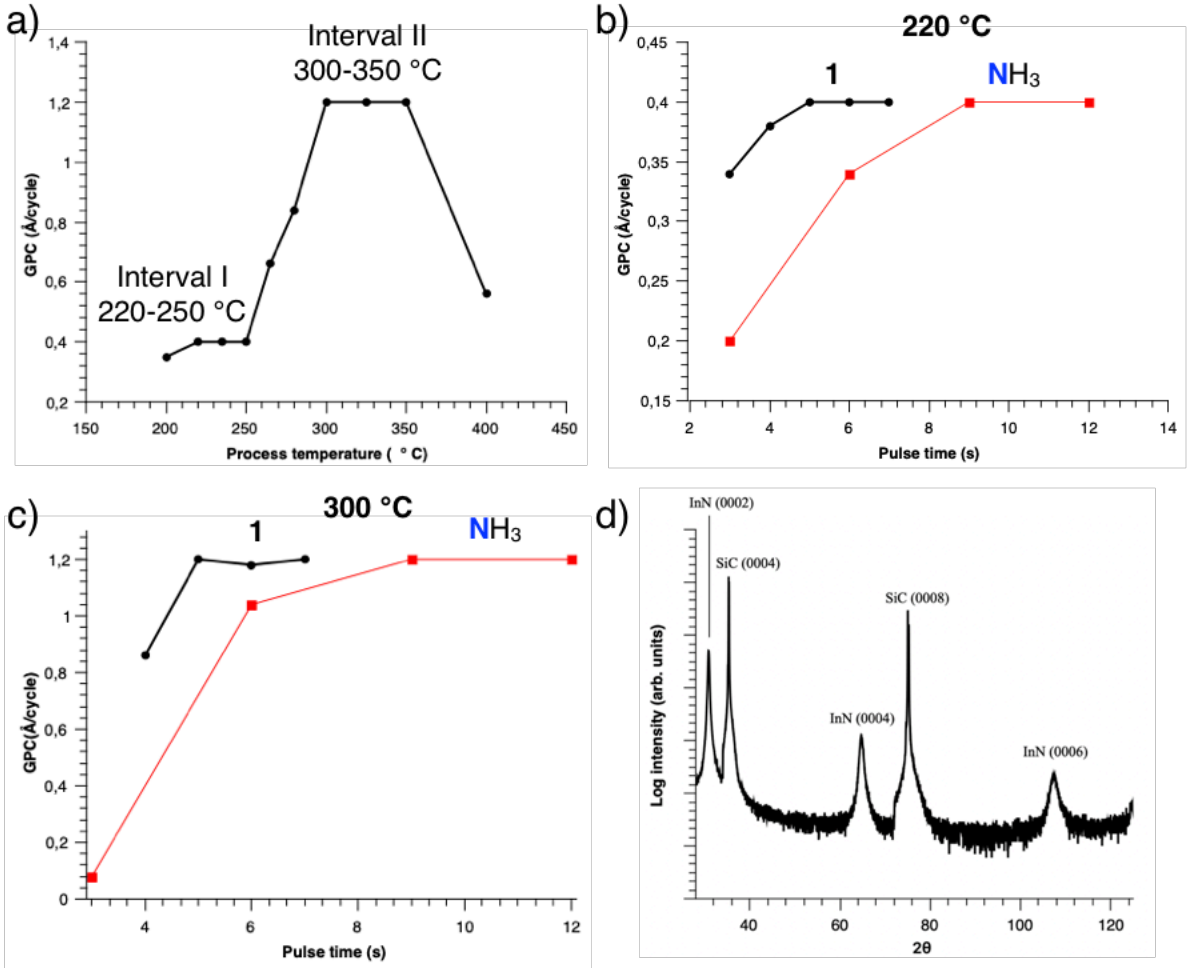

Figure 2. a) The growth dependence on process temperature using **1** and NH_3 plasma. b) The growth per cycle behavior of **1** and NH_3 pulses deposited at 220 °C. c) The growth per cycle behavior of **1** and NH_3 pulses deposited at 300 °C. d) XRD of InN on 4H-SiC (0001) using **1** and NH_3 plasma at 325 °C showing epitaxial InN along the c-axis.